LIXYS 1200V XPT[™] IGBT GenX3[™]

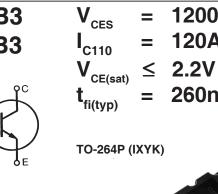
Advance Technical Information

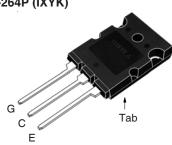
IXYK120N120B3 IXYX120N120B3

High-Speed IGBT for 10-30 kHz Switching

Symbol	Test Conditions	Maximum Ratings			
V _{ces}	$T_{J} = 25^{\circ}C \text{ to } 175^{\circ}C$	1200	V		
V _{CGR}	$T_{J} = 25^{\circ}C$ to 175°C, $R_{GE} = 1M\Omega$	1200	V		
V _{GES}	Continuous	±20	V		
V _{GEM}	Transient	±30	V		
I _{C25}	$T_c = 25^{\circ}C$ (Chip Capability)	320	A		
	Terminal Current Limit	160	А		
I _{C110}	$T_c = 110^{\circ}C$	120	A		
I _{CM}	$T_c = 25^{\circ}C$, 1ms	800	А		
I _A	T _c = 25°C	60	A		
E _{AS}	$T_c = 25^{\circ}C$	2	J		
SSOA	$V_{GE} = 15V, T_{VJ} = 150^{\circ}C, R_{G} = 1\Omega$	I _{CM} = 240	A		
(RBSOA)	Clamped Inductive Load	$V_{ce} \leq V_{ces}$			
P _c	$T_c = 25^{\circ}C$	1500	W		
T,		-55 +175	°C		
T _{JM}		175	°C		
T _{stg}		-55 +175	°C		
T	Maximum Lead Temperature for Soldering	300	°C		
	1.6 mm (0.062in.) from Case for 10s	260	°C		
M _d	Mounting Torque (TO-264)	1.13/10	Nm/lb.in		
F _c	Mounting Force (PLUS247)	20120 /4.527	N/lb		
Weight	TO-264P	10	g		
	PLUS247	6	g		

Symbol (T _J = 25°C, U	Test Conditions Jnless Otherwise Specified)	Characteristic Values Min. Typ. Max.				
BV _{CES}	$I_{c} = 250 \mu A, V_{ge} = 0 V$	1200			V	
$V_{_{GE(th)}}$	I_{c} = 1mA, $V_{ce} = V_{ge}$	3.0		5.0	V	
I _{CES}	$V_{CE} = V_{CES}, V_{GE} = 0V$ $T_{J} = 150^{\circ}C$			25 1.5	μA mA	
I _{GES}	V_{CE} = 0V, V_{GE} = ±20V			±200	nA	
V _{CE(sat)}	I_{c} = 100A, V_{ge} = 15V, Note 1 T_{J} = 150°C		1.8 2.4	2.2	V V	



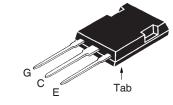


1200V

120A

260ns

PLUS247 (IXYX)



G = Gate = Emitter Е C = Collector Tab = Collector

Features

- Square RBSOA
- International Standard Packages
- · Positive Thermal Coefficient of Vce(sat)
- Avalanche Rated
- High Current Handling Capability

Advantages

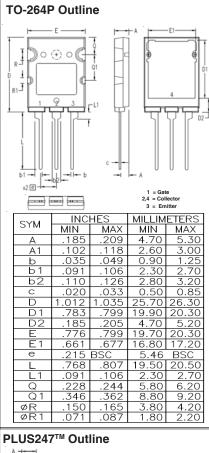
- High Power Density
- Low Gate Drive Requirement

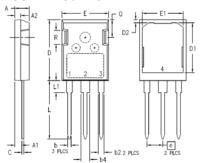
Applications

- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

	Γ	XYS				
		t Conditions	teristic V	eristic Values		
$(T_{J} = 25)$	°C Ur	nless Otherwise Specified)	Min.	Тур.	Max.	
g _{fs}		$I_{c} = 60A, V_{ce} = 10V, Note 1$	40	70	S	
C _{ies})			9800	pF	
C _{oes}	}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		567	pF	
C _{res}	J			215	pF	
Q _{g(on)}				400	nC	
Q _{ge}	}	$I_{c} = I_{c110}, V_{ge} = 15V, V_{ce} = 0.5 \bullet V_{ces}$		70	nC	
Q _{gc}	J			190	nC	
t _{d(on)})			30	ns	
t _{ri}		Inductive load, T _{.1} = 25°C		54	ns	
E _{on}		$I_{c} = 100A, V_{GE} = 15V$		9.7	mJ	
t _{d(off)}	Ì	$V_{cE} = 0.8 \cdot V_{cES}, R_{g} = 1\Omega$		340	ns	
t _{fi}		Note 2		260	ns	
E _{off}	J			21.5	mJ	
t _{d(on)})			29	ns	
t _{ri}		Inductive load, T _J = 150°C		55	ns	
E _{on}		I _c = 100A, V _{ge} = 15V		14.7	mJ	
t _{d(off)}	($V_{ce} = 0.8 \bullet V_{ces}, R_{g} = 1\Omega$		420	ns	
t _{ri}		Note 2		406	ns	
E _{off}	J			27.9	mJ	
R _{thJC}					0.10 °C/W	
R _{thCS}				0.15	°C/W	

IXYK120N120B3 IXYX120N120B3





Terminals: 1 - Gate 2,4 - Collector

SYM	INC	HES	MILLIMETERS			
SIM	MIN	MAX	MIN	MAX		
А	.190	.205	4.83	5.21		
A1	.090	.100	2,29	2.54		
A2	.075	.085	1.91	2.16		
b	.045	.055	1.14	1.40		
b2	.075	.087	1.91	2.20		
b4	.115	.126	2.92	3.20		
С	.024	.031	0.61	0.80		
D	.819	.840	20.80	21.34		
D1	.650	.690	16.51	17.53		
D2	.035	.050	0.89	1.27		
E	.620	.635	15.75	16.13		
E1	.520	.560	13.08	14.22		
е	.215	BSC	5.45	5.45 BSC		
L	.780	.810	19.81	20,57		
L1	.150	.170	3.81	4.32		
Q	.220	.244	5.59	6.20		
R	.170	.190	4.32	4,83		

Notes:

- 1. Pulse test, t \leq 300µs, duty cycle, d \leq 2%.
- 2. Switching times & energy losses may increase for higher V_{ce} (clamp), T_{J} or R_{g} .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the	Bight to Change	limite T	Lest Conditions	and Dimensions
INTO Reserves life	night to Change	ELITTING, I	rest Conditions,	and Dimensions.

IXYS MOSFETs and IGBTs are covered 4,835,					6,404,065 B1				
by one or more of the following U.S. patents: 4,860,	72 5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,	06 5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	



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